



STP4N150 - STF4N150 STW4N150

N-CHANNEL 1500V - 5Ω - 4A TO-220/TO-220FP/TO-247
Very High Voltage PowerMESH™ MOSFET

PRODUCT PREVIEW

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STF4N150	1500 V	< 7 Ω	4 A (*)	40 W
STP4N150	1500 V	< 7 Ω	4 A	160 W
STW4N150	1500 V	< 7 Ω	4 A	160 W

- TYPICAL R_{DS(on)} = 5 Ω
- AVALANCHE RUGGEDNESS
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- HIGH SPEED SWITCHING

DESCRIPTION

Using the well consolidated high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of Power MOSFETs with outstanding performances. The strengthened layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, unrivalled gate charge and switching characteristics.

APPLICATIONS

- SWITCH MODE POWER SUPPLIES

Figure 1: Package

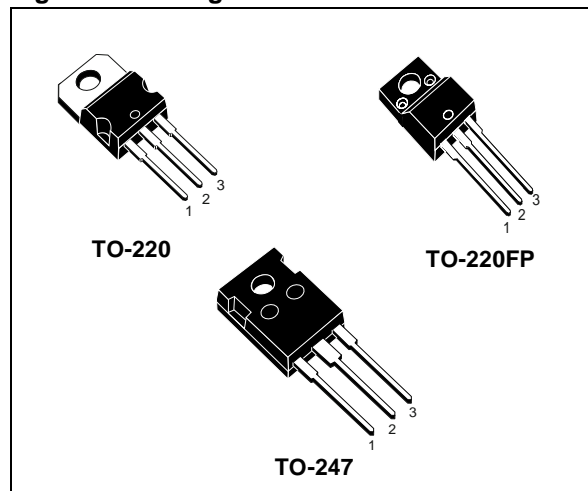


Figure 2: Internal Schematic Diagram

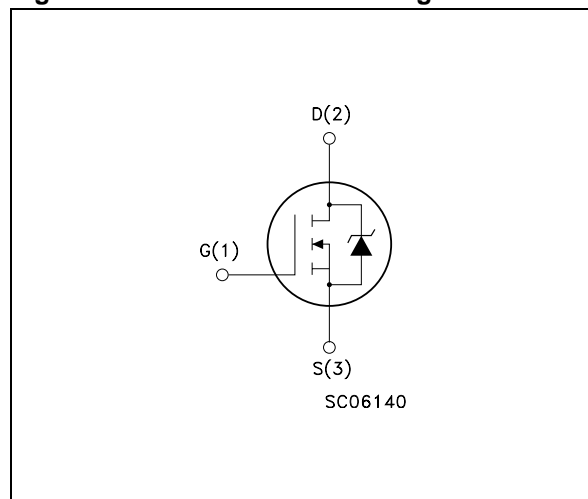


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STF4N150	F4N150	TO-220FP	TUBE
STP4N150	P4N150	TO-220	TUBE
STW4N150	W4N150	TO-247	TUBE

Rev. 1

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value		Unit
		STP4N150 STW4N150	STF4N150	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	1500		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	1500		V
V _{GS}	Gate- source Voltage	± 30		V
I _D	Drain Current (continuous) at T _C = 25°C	4	4 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	2.5	2.5 (*)	A
I _{DM} (●)	Drain Current (pulsed)	12	12 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	160	40	W
	Derating Factor	1	0.24	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T _j T _{stg}	Operating Junction Temperature Storage Temperature	-55 to 150 -55 to 150		°C °C

(●) Pulse width limited by safe operating area
 (*) Limited only by maximum temperature allowed

Table 4: Thermal Data

		TO-220	TO-220FP	TO-247	
R _{thj-case}	Thermal Resistance Junction-case Max	0.78	3.1	0.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		50	°C/W

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 5: On /Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 1 mA, V _{GS} = 0	1500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125°C			10 500	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 2 A		5	7	Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 6: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 30\text{ V}$, $I_D = 2\text{ A}$		TBD		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		1300 120 12		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off-Delay Time Fall Time	$V_{DD} = 750\text{ V}$, $I_D = 2\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 4)		35 30 45 45		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 600\text{ V}$, $I_D = 4\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 7)		30 10 9	50	nC nC nC

Table 7: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				4 12	A A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 4\text{ A}$, $V_{GS} = 0$			2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 45\text{ V}$ (see Figure 5)		510 3 12		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 45\text{ V}$, $T_j = 150^\circ\text{C}$ (see Figure 5)		650 4 12.6		ns μC A

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

Figure 3: Unclamped Inductive Load Test Circuit

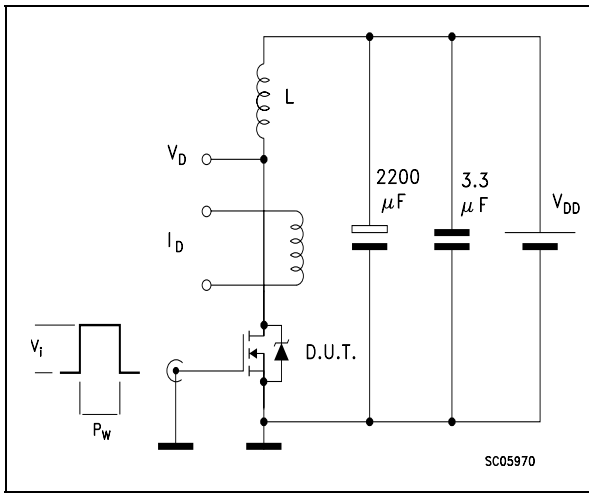


Figure 4: Switching Times Test Circuit For Resistive Load

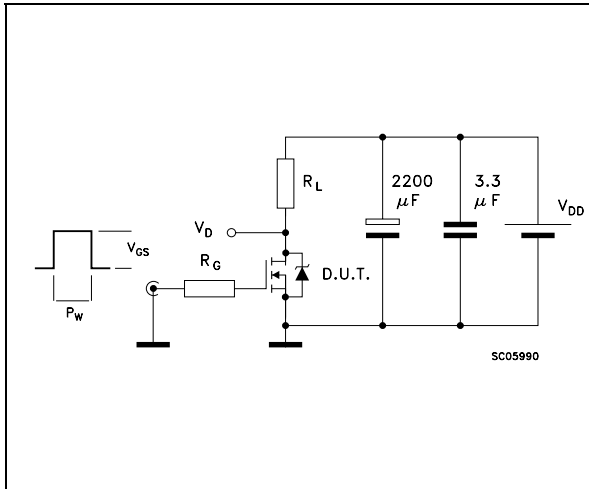


Figure 5: Test Circuit For Inductive Load Switching and Diode Recovery Times

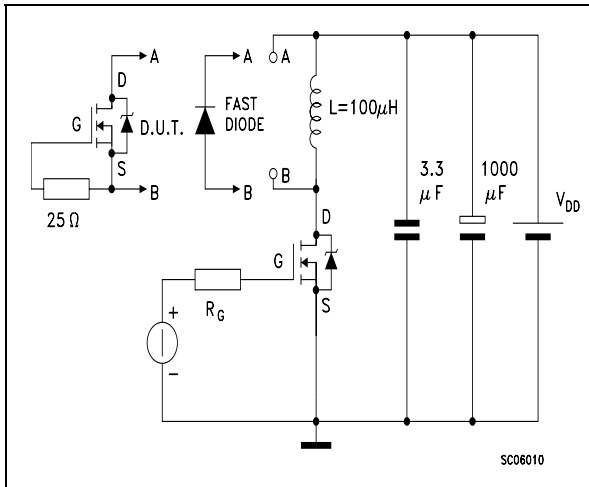


Figure 6: Unclamped Inductive Waveform

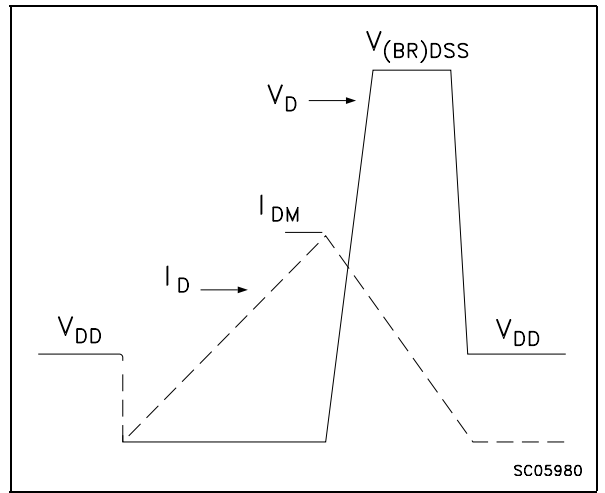
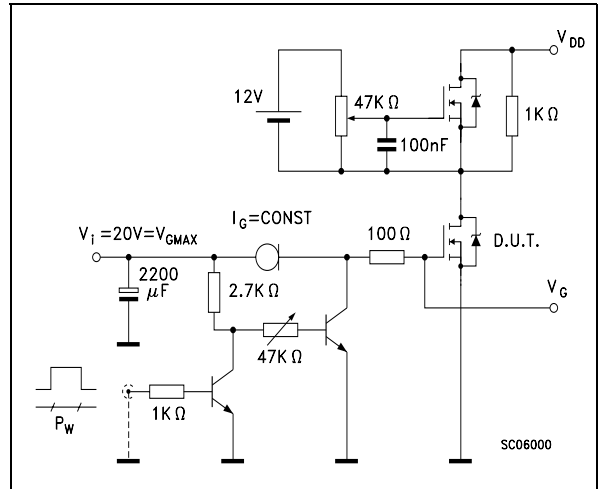
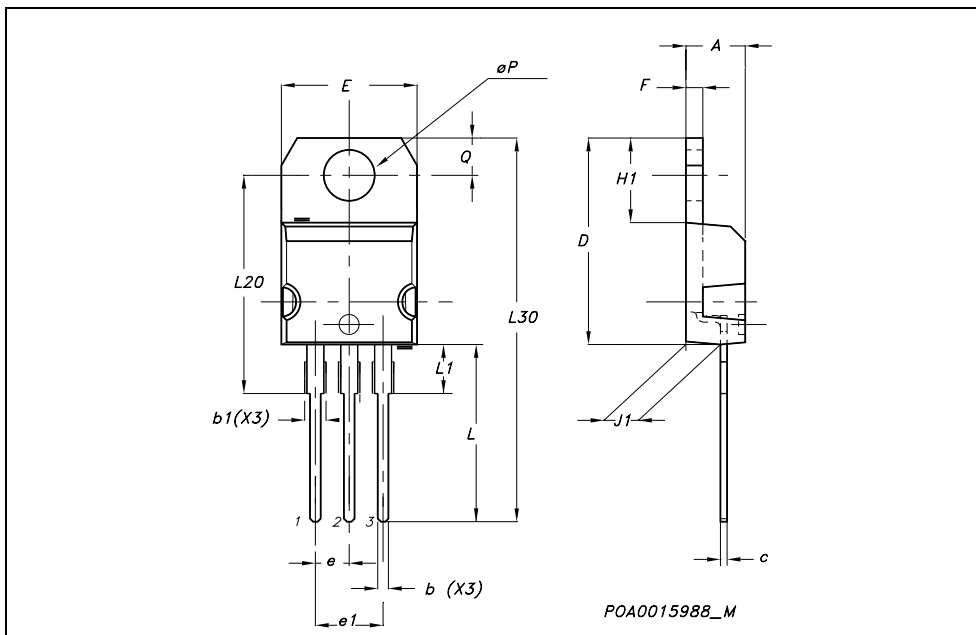


Figure 7: Gate Charge Test Circuit



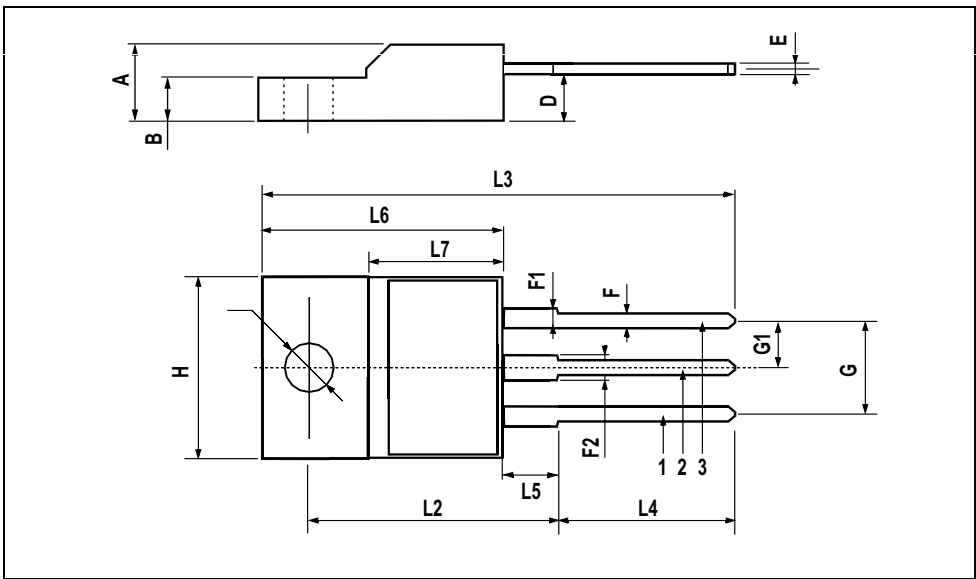
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

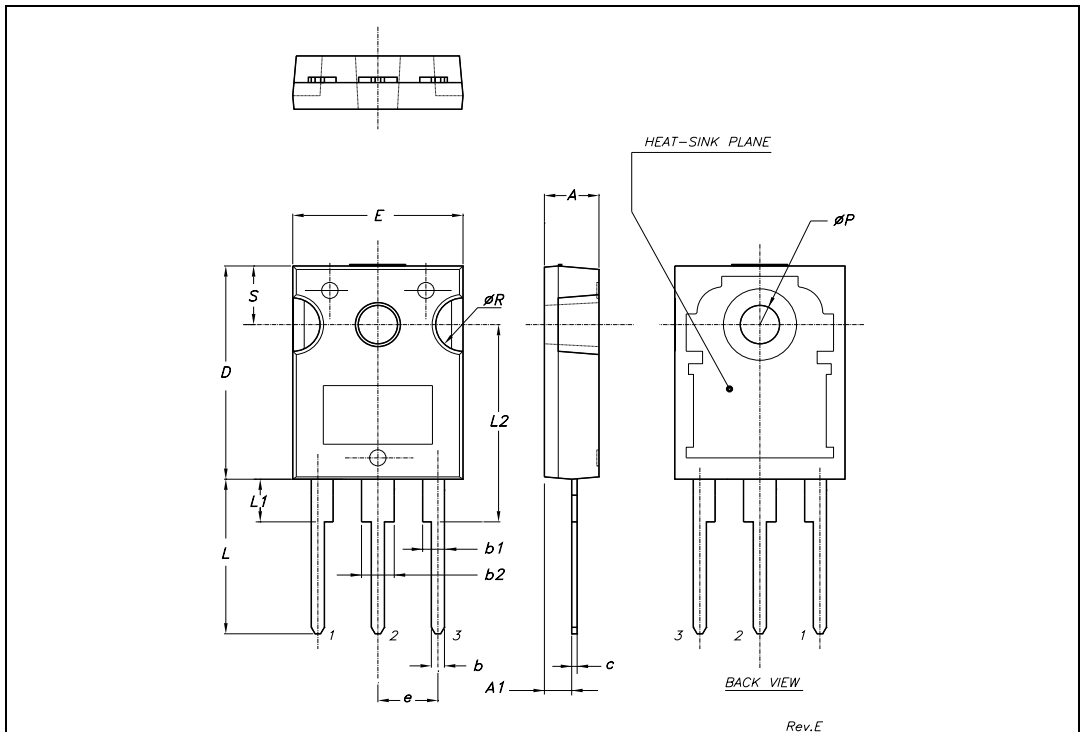


Table 8: Revision History

Date	Revision	Description of Changes
11-Mar-2005	1	First release.

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